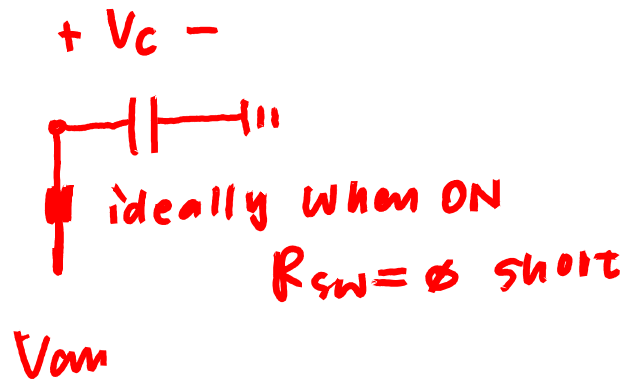
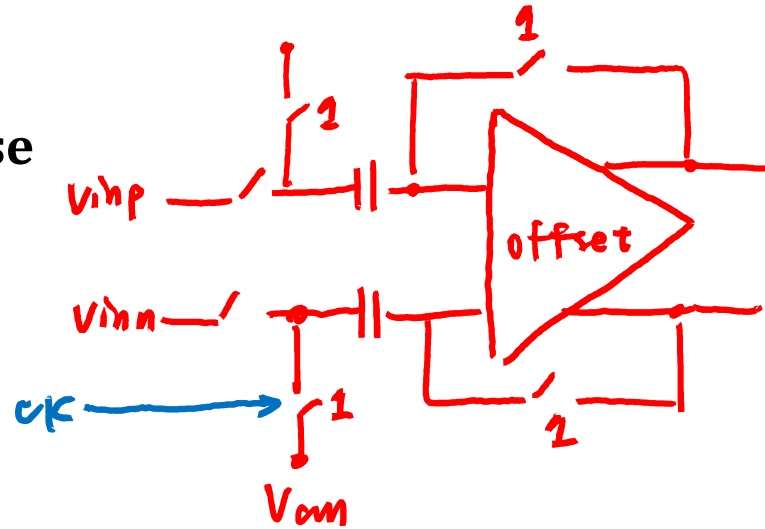


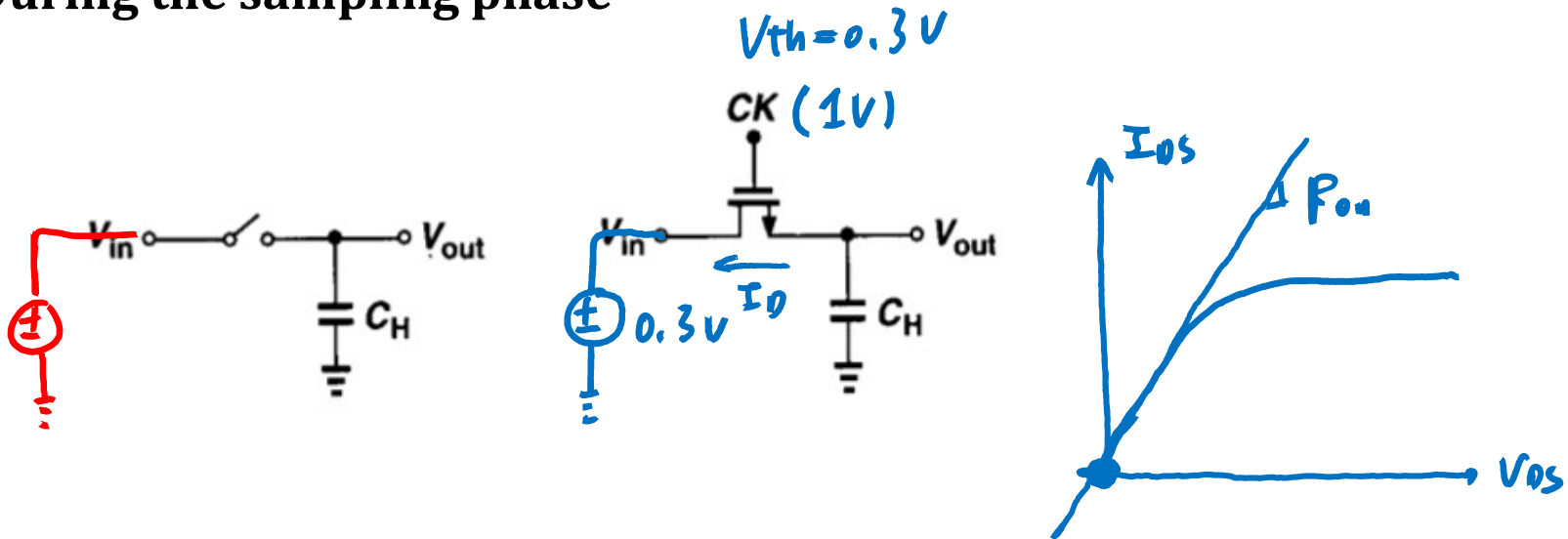
# Switches

- ◆ During the sampling phase *offset*



# Switches

- ◆ During the sampling phase



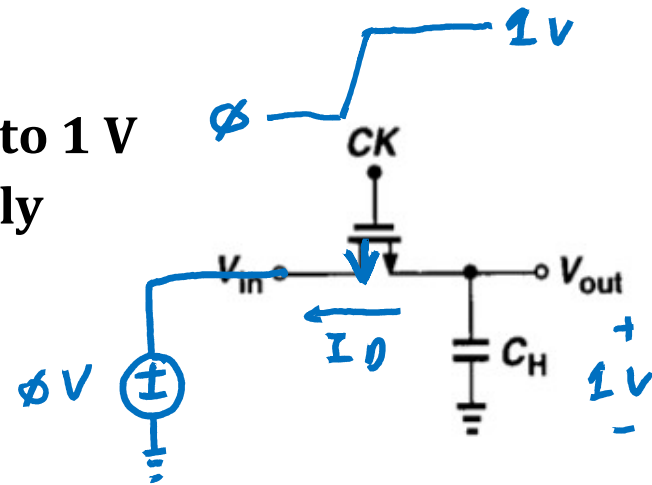
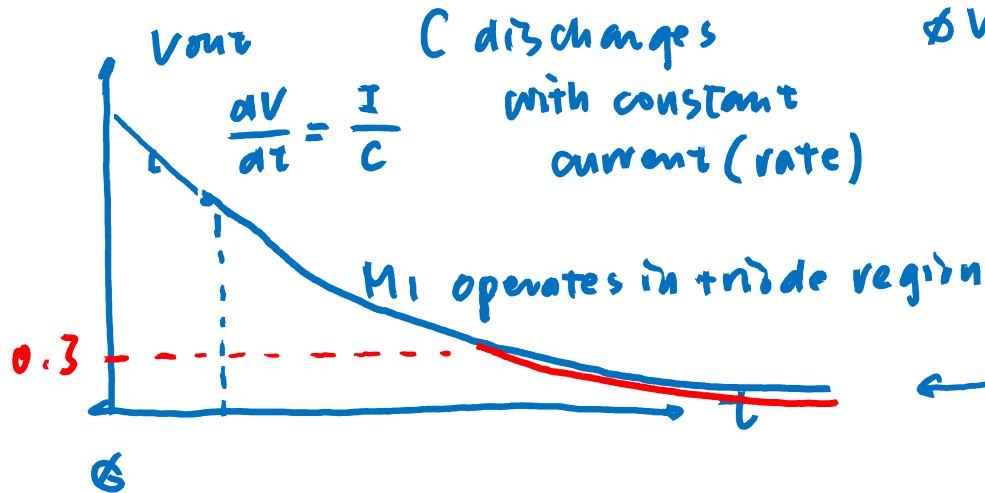
- With VCK of some high value,  $V_{th}$  of 0.3 V, and  $V_{in}$  of 0.3 V
- Once reaching steady state
  - $V_{out} = 0.3$
  - The transistor current =  $\emptyset$  *the transistor is ON, but flows no current*
  - The transistor operating in *deep triode region with certain  $R_{on}$*
- With  $VCK=0$  *the switch is turned OFF*

# Switches – A Few Cases (I)

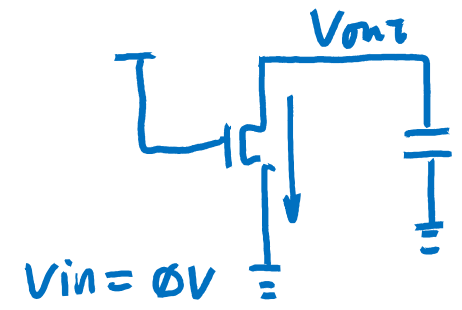
◆  $V_{th}$  of 0.3 V and VCK goes from 0 V to 1 V

1.  $V_{in} = 0$  V while  $V_{out} = 1.0$  V initially

Initially  $M_1$  in sat.



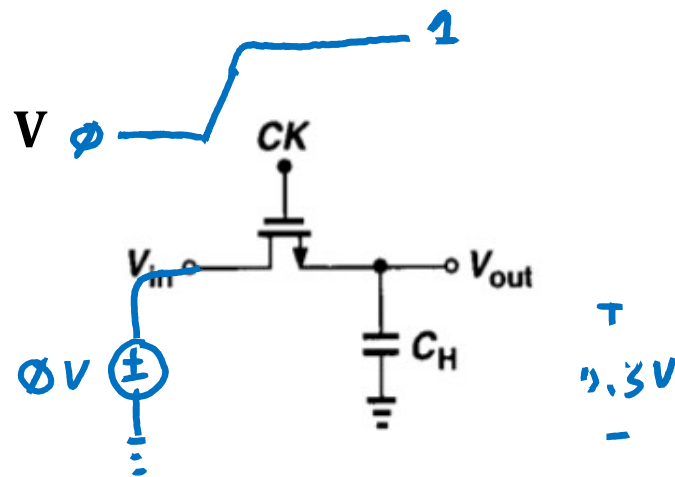
← as  $t \rightarrow \infty$   
 $M_1$  in deep triode region  
 $I_D \rightarrow 0$



- Through the settling transient
  - The transistor current direction
  - The transistor operating region

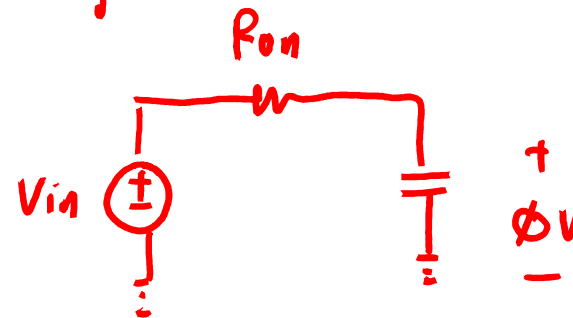
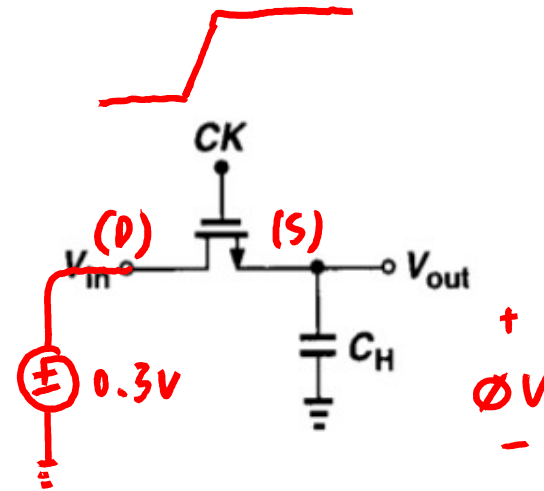
## Switches – A Few Cases (II)

- ◆  $V_{th}$  of 0.3 V and  $V_{CK}$  goes from 0 V to 1 V
- 1.  $V_{in} = 0$  V while  $V_{out} = 1.0$  V initially
- 2.  $V_{in} = 0$  V while  $V_{out} = 0.3$  V initially



## Switches – A Few Cases (III)

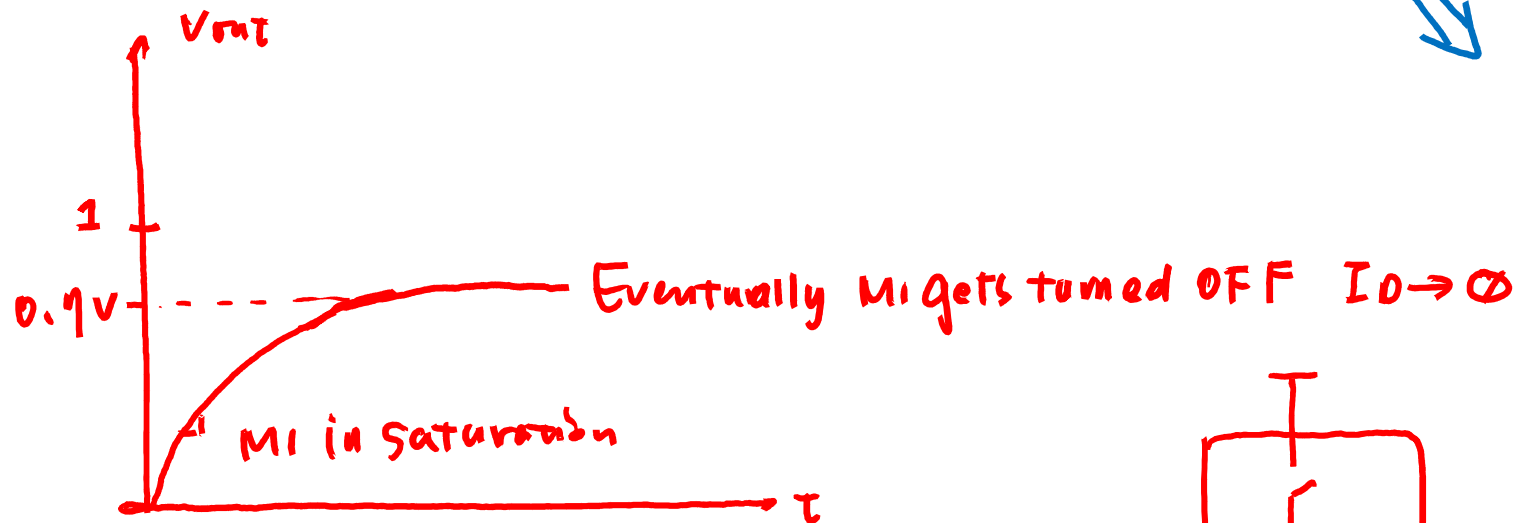
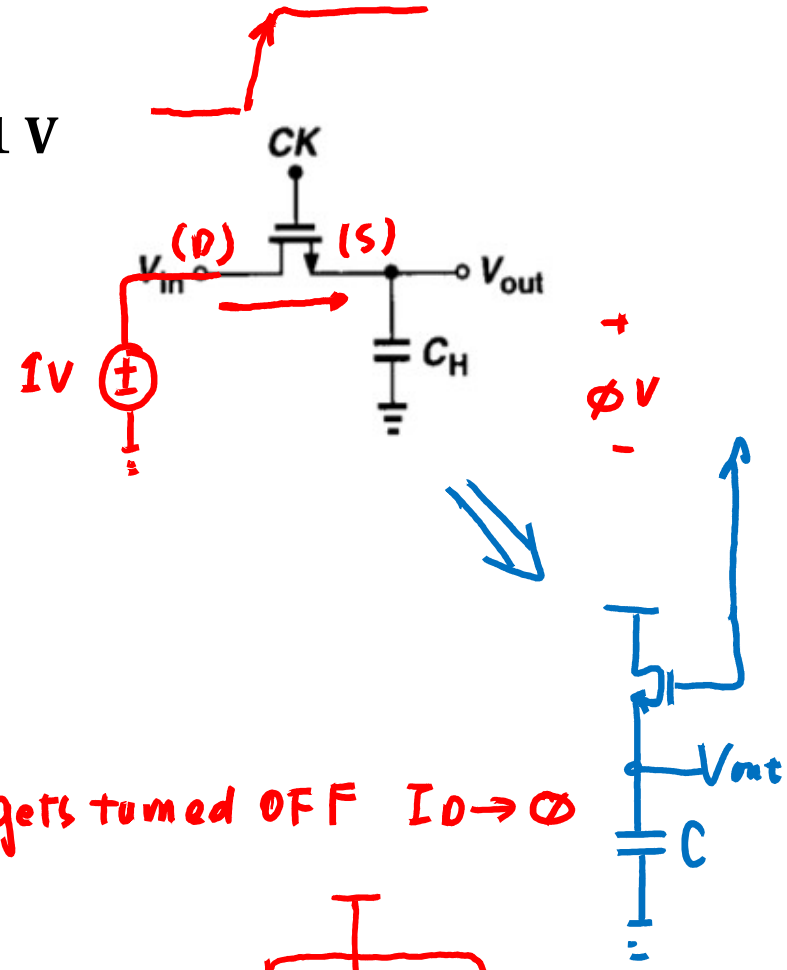
- ◆  $V_{th}$  of 0.3 V and  $V_{CK}$  goes from 0 V to 1 V
- 1.  $V_{in} = 0$  V while  $V_{out} = 1.0$  V initially
- 2.  $V_{in} = 0$  V while  $V_{out} = 0.3$  V initially
- 3.  $V_{in} = 0.3$  V while  $V_{out} = 0$  V initially



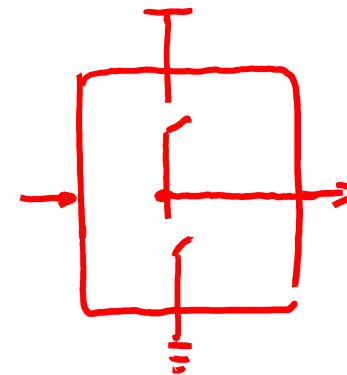
- Through the settling transient
  - The transistor current direction
  - The transistor operating region

# Switches – A Few Cases (IV)

- ◆  $V_{th}$  of 0.3 V and  $V_{CK}$  goes from 0 V to 1 V
- 1.  $V_{in} = 0$  V while  $V_{out} = 1.0$  V initially
- 2.  $V_{in} = 0$  V while  $V_{out} = 0.3$  V initially
- 3.  $V_{in} = 0.3$  V while  $V_{out} = 0$  V initially
- 4.  $V_{in} = 1.0$  V while  $V_{out} = 0$  V initially

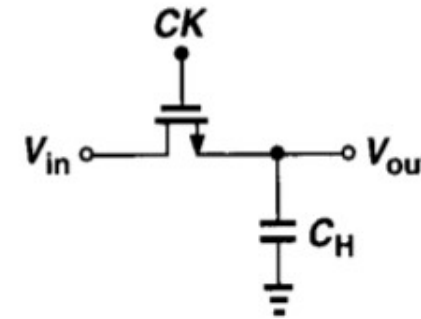


$$\frac{dV}{dt} = \frac{I}{C} = f(V_{gs}) = f(V_{DD} - V_{out})$$



## Switches – A Few Cases (IV)

- ◆  $V_{th}$  of 0.3 V and  $V_{CK}$  goes from 0 V to 1 V
- 4.  $V_{in} = 1.0$  V while  $V_{out} = 0$  V initially

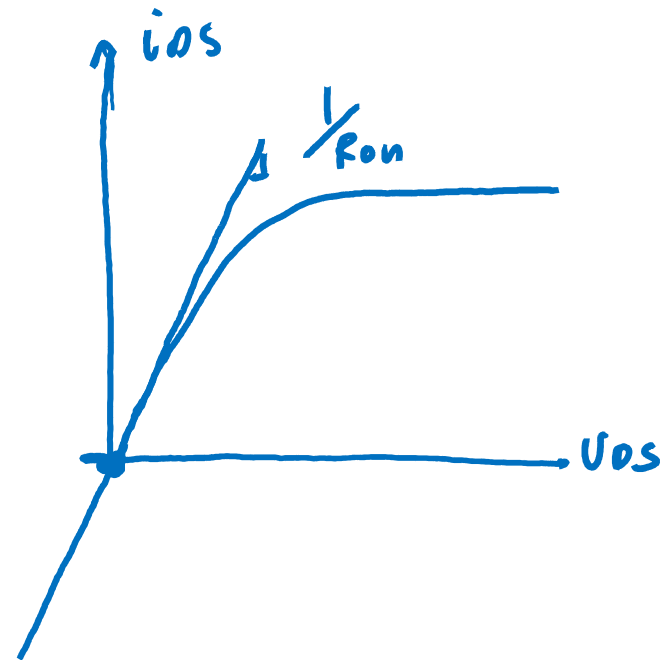
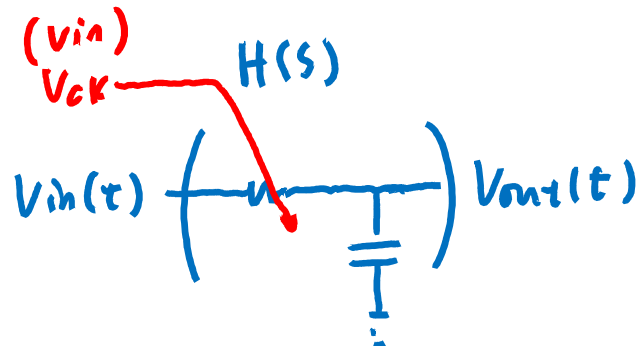
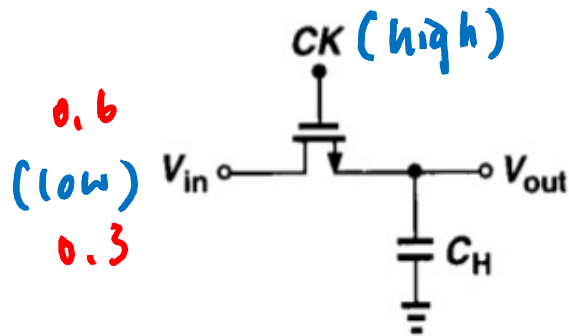


- Through the settling transient
  - The transistor current direction
  - The transistor operating region

# On Resistance

- Can be viewed as a resistor equal to

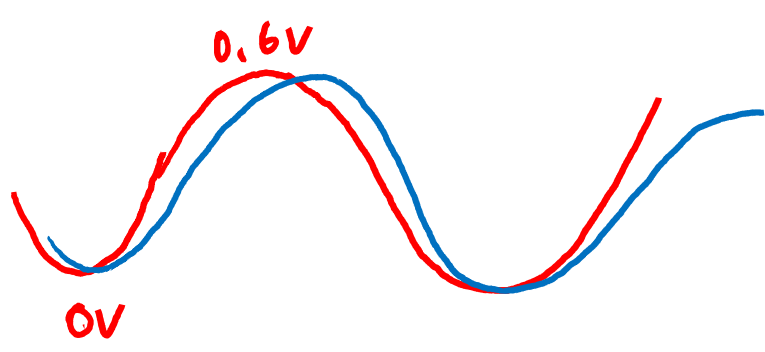
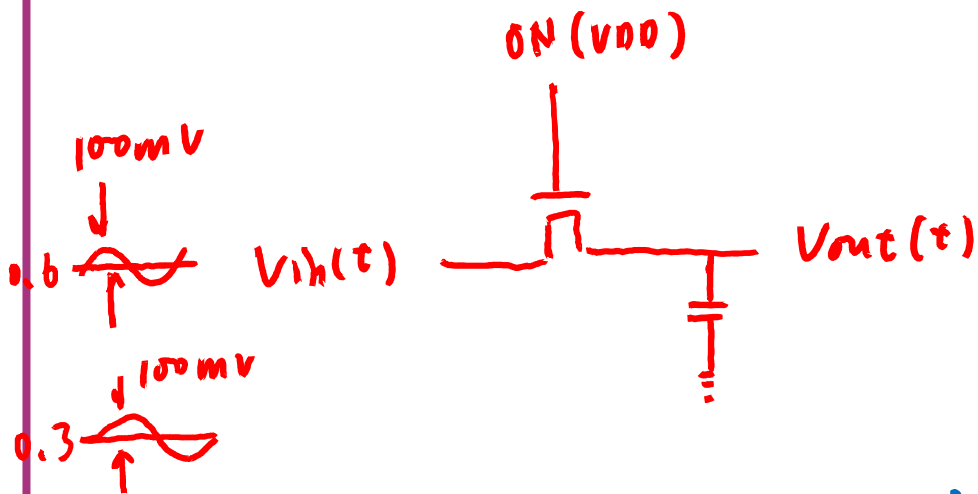
$$R_{on} = \left( \mu C_{ox} \frac{W}{L} (V_{CK} - V_{in} - V_{th}) \right)^{-1}$$



$$H(s) = \frac{\frac{1}{sC}}{R + \frac{1}{sC}} = \frac{1}{1 + sRC}$$

- On-resistance and speed depend on the input level

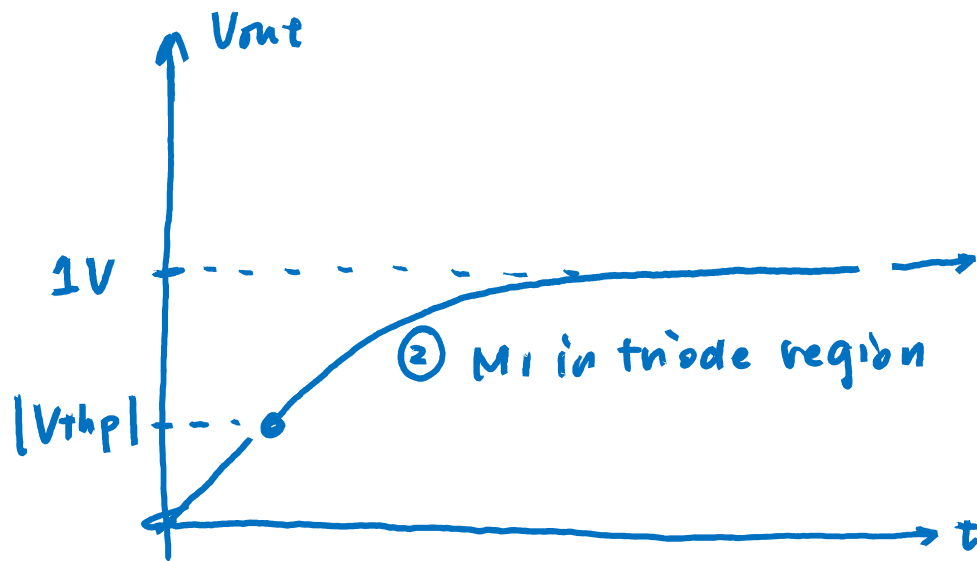




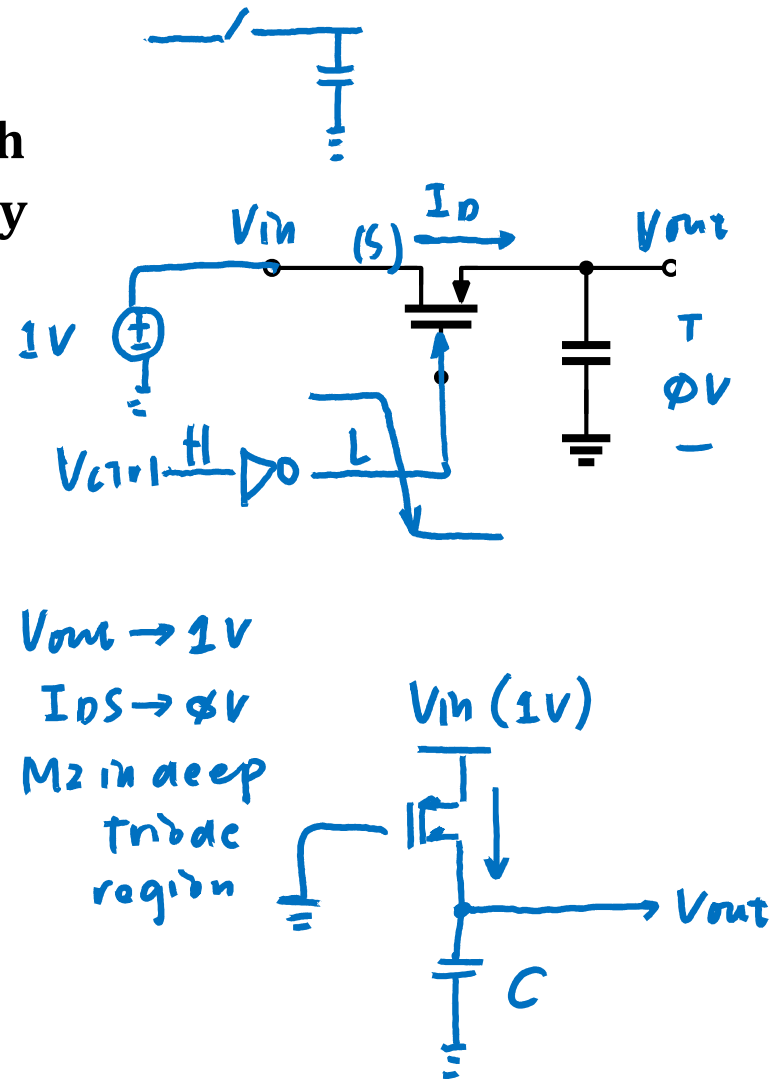
Nonlinearity  
 Small-signal operation  
 bias point matters  
 (common-mode)  
 Large-signal operation  
 waveform distortion

# Using PMOS as Switch (I)

- ◆ VCK goes down to turn on the switch
- 1.  $V_{in} = 1.0\text{ V}$  while  $V_{out} = 0\text{ V}$  initially

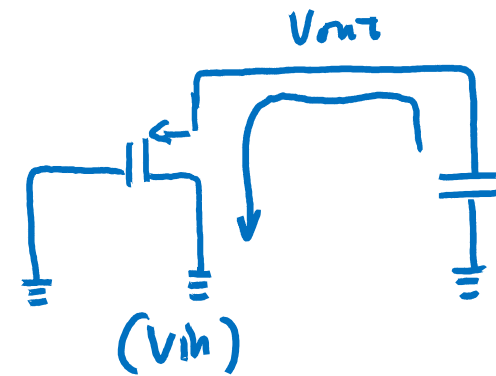
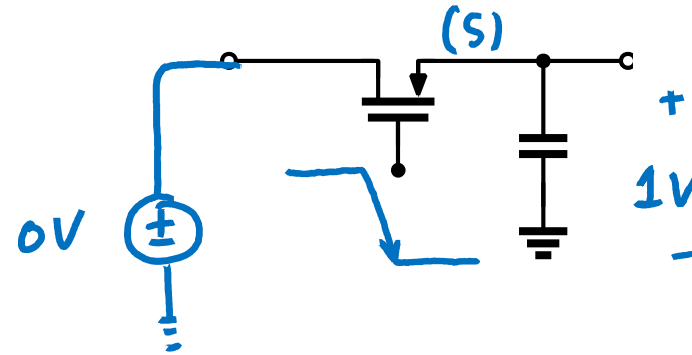


① Initially  $M_1$  in saturation



# Using PMOS as Switch (II)

- ◆ VCK goes down to turn on the switch
- 2. Vin = 0 V while Vout = 1.0 V initially

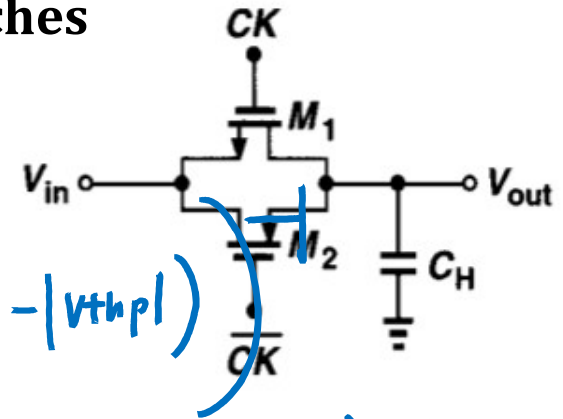


$$R_{on,p} = \left( \mu C_{ox} \frac{W}{L} (V_{in} - 0V - |V_{thp}|) \right)^{-1}$$

# Pass Transistors

- ◆ **Transmission gates or Complementary switches**

- Complementary clock signals needed



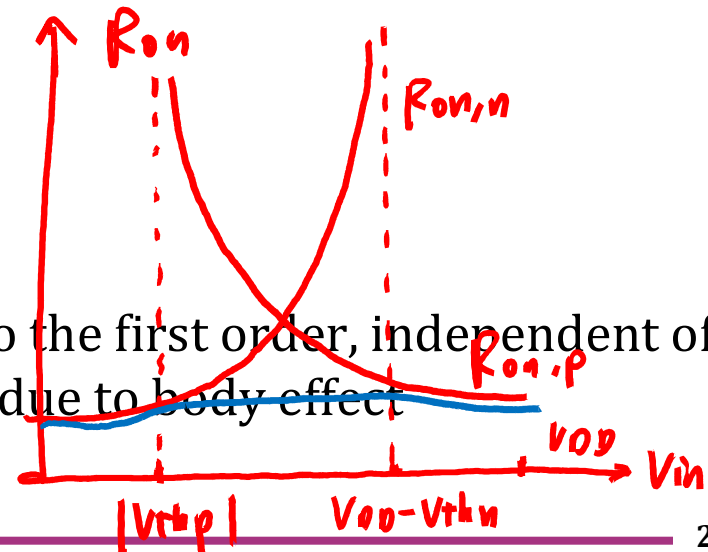
$$R_{on,eff} = R_{on,n} \parallel R_{on,p}$$

$$= \left( \mu_n C_{ox} \frac{W}{L_n} (V_{DD} - V_{in} - V_{thn}) + \mu_p C_{ox} \frac{W}{L_p} (V_{in} - |V_{thp}|) \right)^{-1}$$

$$= \left( (\mu_p C_{ox} \frac{W}{L_p} - \mu_n C_{ox} \frac{W}{L_n}) V_{in} + \mu_n C_{ox} \frac{W}{L_n} (V_{DD} - V_{thn}) - \mu_p C_{ox} \frac{W}{L_p} |V_{thp}| \right)^{-1}$$

$$\Rightarrow \frac{\mu_p C_{ox,p} \frac{W}{L_p}}{\mu_n C_{ox,n} \frac{W}{L_n}} = 1 \Rightarrow \frac{\frac{W}{L_p}}{\frac{W}{L_n}} \approx \frac{\mu_n}{\mu_p}$$

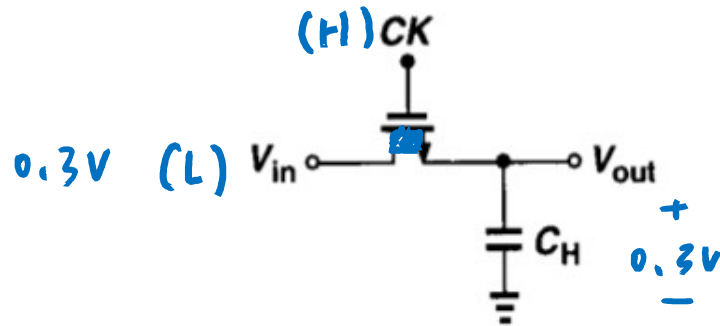
- Can be sized so that the on-resistance is, to the first order, independent of the input level  $\rightarrow$   $V_{thp}$  and  $V_{thn}$  still vary due to body effect



# Charge Injection

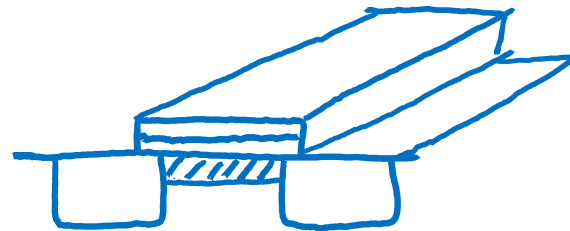
◆ In order to reduce Ron and speed up the operation

- 1) Rail-to-rail clock signals needed
- 2) Large transistors
- 3) Smaller holding capacitor



inversion layer  
 $Q = CV$  其中  $C = WL \cdot C_{ox}$

$$Q_{ch} = WLC_{ox}(V_{DD} - V_{in} - V_{TH})$$

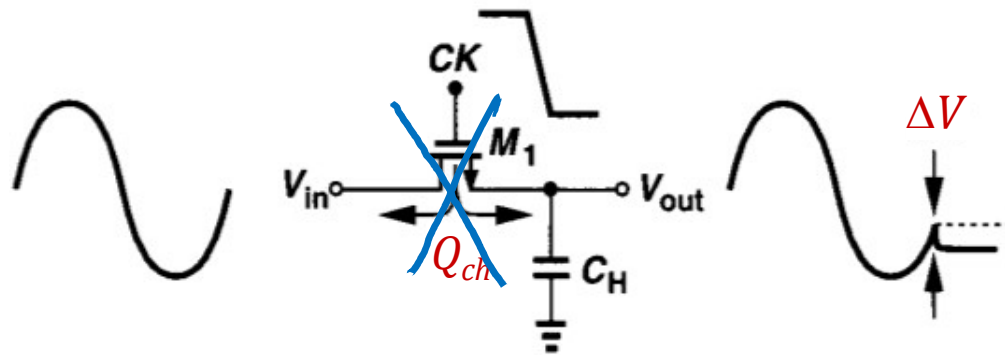


- Charge in the channel when ON

# Charge Injection

◆ In order to reduce Ron and speed up the operation

- 1) Rail-to-rail clock signals needed
- 2) Large transistors
- 3) Smaller holding capacitor



$$Q_{ch} = WLC_{ox}(V_{DD} - V_{in} - V_{TH})$$

$$\Delta V = \frac{WLC_{ox}(V_{DD} - V_{in} - V_{TH})}{C_H}$$

- Charge in the channel when ON
- Causing a pedestal at the output when turning OFF

